

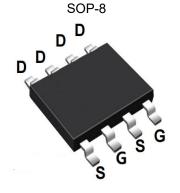


1. Features

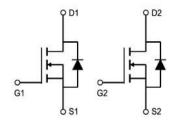
- Advanced trench cell design
- Low Thermal Resistance
- · Low Gate Charge

2. Mechanical Data

- Case:Molded Plastic,SOP-8.
- Epoxy:UL 94V-0 rate flame retardant
- Terminals:Plated Leads Solderable perMIL-STD-750,Method-2026.
- Marking:XNM10N03ST
- Mounting Position : Any.



- 1 Gate
- 2 Source
- 3 Drain



3. Maximum Ratings and Electrical Characteristics

Rating at 25℃ ambient temperature unless otherwise specified.

Parameter		Symbol	Value	UNIT	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current	T _A = 25℃		10	Α	
	T _A = 70°C	- I _D	8	A	
Drain Current-Pulsed ¹		I _{DM}	55	Α	
Avalanche Current		I _{AS}	22	Α	
Single Pulse Avalanche Energy ¹		E _{AS}	24	mJ	
Power Dissipation		P _{tot}	2	W	
Thermal Resistance from Junction to Lead		$R_{\theta JL}$	40	°C/W	
Thermal Resistance from Junction to Ambient ²		R _{eJA}	62.5	°C/W	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +150	$^{\circ}$	



4. Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Off Characteristics						
Drain-source breakdown voltage	V(BR) DSS	V _G s = 0V, I _D =250µA	30			V
Zero gate voltage drain current	loss	V _{DS} =30V			1	μA
Gate-source leakage current	Igss	V _{GS} =±20V			±100	nA
On characteristics ³						
	Dans,	Vgs =10V, ID =10A		10.8	13	mΩ
Drain-source on-resistance	RDS(on)	Vgs =4.5V, ID =5A		14	17.5	mΩ
Forward tranconductance	grs	V _{DS} =5V, I _D =10A		43		S
Gate threshold voltage	V _G S(th)	V _{DS} =V _{GS} , I _D =250µA	1		2.5	V
Dynamic Characteristics ⁴				-		
Gate resistance	R_{g}	$V_{DS} = 0 \text{ V}, V_{GS} = 0 \text{V}, f = 1 \text{ MHz}$			2.4	Ω
Input capacitance	Ciss			760		pF
Output capacitance	Coss	V _{DS} =15V,V _{GS} =0V,f =1MHz		125		pF
Reverse transfer capacitance	Crss			70		pF
Switching Characteristics ⁴						
Onto the same total	Q_g	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}, V_{GS} = 4.5 \text{ V}$		6.6		nC
Gate charge total				14		IIC
Gate-Source Charge	Q_gs	V _{DS} =15V,I _D =10A,V _{GS} =10V		2.4		nC
Gate-Drain Charge	Q_{gd}			3		nC
Turn-on delay time	td(on)			4.4		nS
Turn-on rise time	tr	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{V},$		9		nS
Turn-off delay time	td(off)	$R_L = 1.5 \Omega$, $R_{GEN} = 3 \Omega$		17		nS
Turn-off fall time	tf			6		nS
Source-Drain Diode characteristi	cs ⁴					
Body Diode Voltage	VsD	Is=1A,V _G s=0V			1	V
Body Diode Reverse Recovery Tim	trr	I _F =10A, di/dt = 100 A / μs		7		nS
Body Diode Reverse Recovery Charge	Qrr	I _F =10A, di/dt = 100 A / μs		8		nC

Notes:

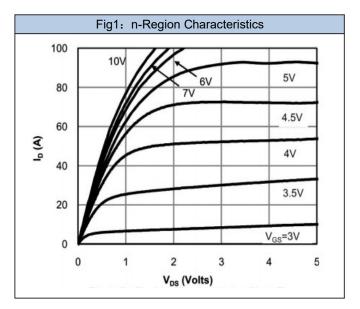
The value in any given application depends on the user's specific board design.

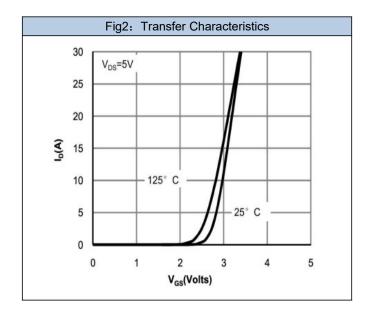
^{1.}Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150 $^{\circ}$ C. Ratings are based on low frequency and duty cycles to keep initial T_J =25 $^{\circ}$ C

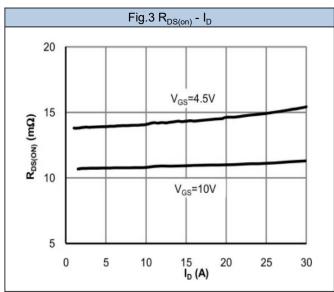
^{2.}The value of R $_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T $_A$ =25 $^{\circ}$ C

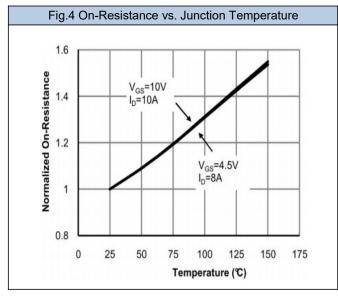


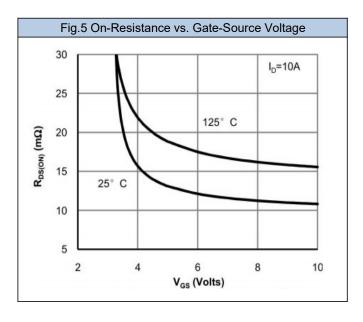
5. Rating And Characteristic Curves

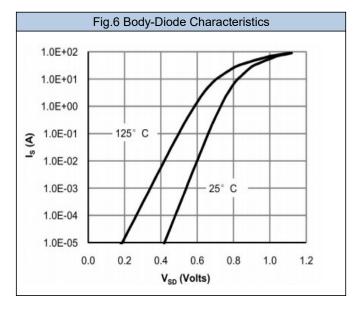






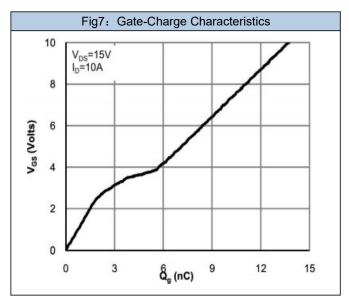


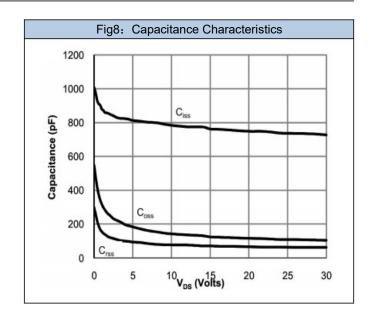


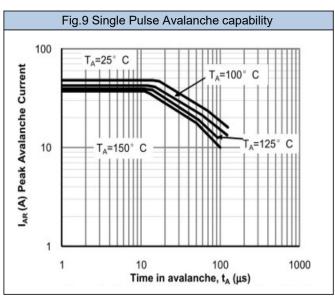


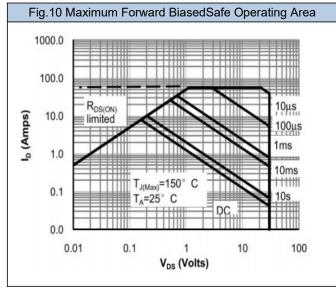


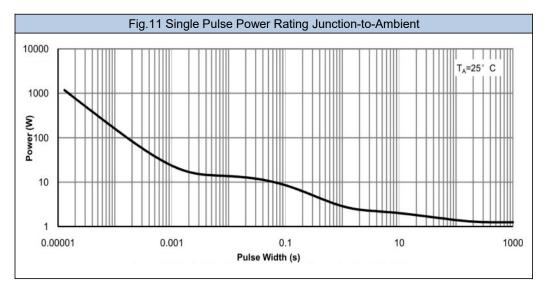
5. Rating And Characteristic Curves





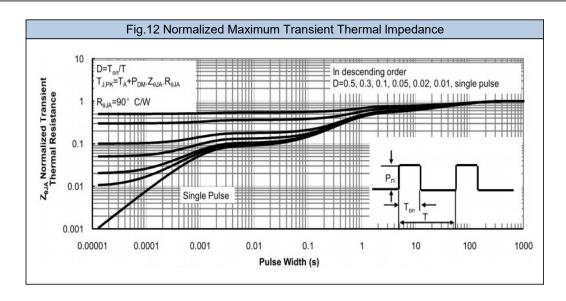






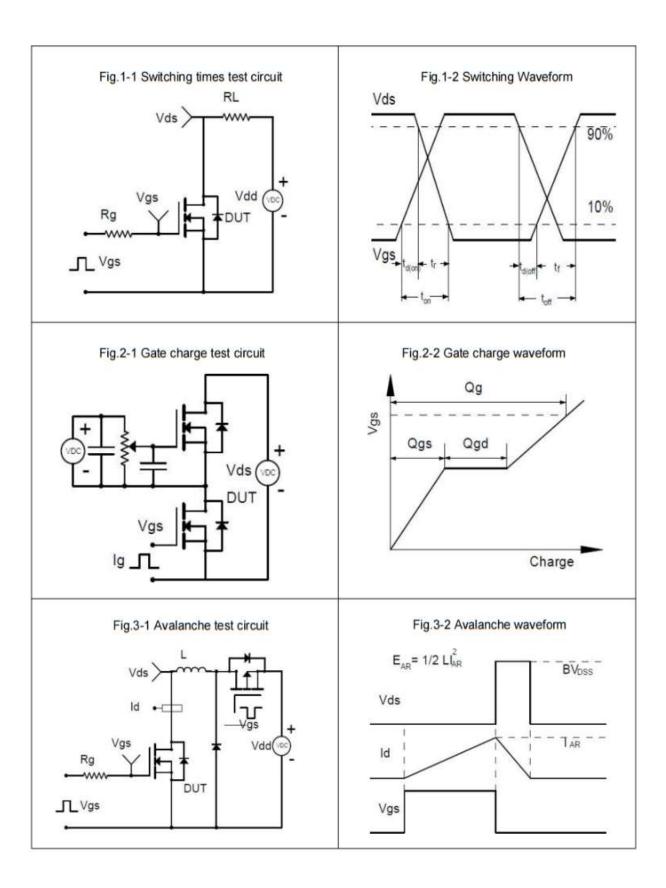


5. Rating And Characteristic Curves



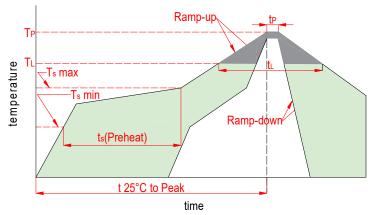


6. Test Circuits



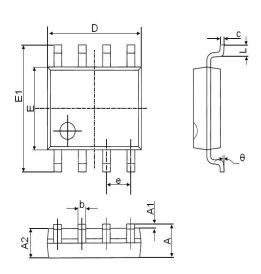


7. Soldering Parameters



Reflow Condition		Lead-free	
	Temp. min(T _s (min))	150℃	
Pre Heat	Temp. max(T _s (min))	200℃	
	Time(min to max)(t _s)	60~180s	
Aver. ramp up rate(Liquidus Temp.)(T _L)to peak		3℃/s max	
T _S (max) to	o T _L -Ramp-up Rate	3℃/s max	
Reflow	Temp.(T _L)(Liquidus)	217 ℃	
	Temp.(t _L)(Liquidus)	60~150s	
Peak Tem	np.(T _P)	260 ^{+0/-5} ℃	
Time with	in actual peak Temp.(t _p)	30s max	
Ramp-down Rate		6℃/s max	
Time 25℃ to peak Tempe.(T _p)		8 minutes max	
Do not exceed		260℃	

8. Dimensions



Dimensions	Inches		Millimeters		
Difficitsions	Min	Max	Min	Max	
Α	0.053	0.069	1.350	1.750	
A1	0.004	0.010	0.100	0.250	
A2	0.053	0.061	1.350	1.550	
b	0.012	0.020	0.300	0.510	
С	0.007	0.009	0.170	0.230	
D	0.185	0.201	4.700	5.100	
E	0.150	0.161	3.800	4.100	
E1	0.228	0.244	5.800	6.200	
е	0.050(BSC)		1.270(BSC)		
L	0.016	0.031	0.400	0.800	
θ	0°	8°	0°	8°	

9. Package Information

Package	Part Number	Marking Code
SOP-8	XNM10N03ST	XNM10N03ST



Important Notice and Disclaimer

- · Reproducing and modifying information of the document is prohibited without from XINNUO.
- XINNUO reserves the right to make changes to this document and its products and specifications.
- XINNUO disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- XINNUO does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the here in document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications.XINNUO makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown her are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify XINNUO for any damages resulting from such improper use or sale.
- Since XINNUO uses lot number as the tracking base, please provide the lot number for tracking when complaining.